

Specifications

Part Number	FQA8N80C_F109
Manufacturer	Fairchild/ON Semiconductor
Description	MOSFET N-CH 800V 8.4A TO-3P
Category	Discrete Semiconductor Products > Transistors - FETs,
Part Status	2663 pcs Stock
Vgs(th) (Max) @ Id	5V @ 250μA
Technology	MOSFET (Metal Oxide)
Supplier Device Package	TO-3PN
Series	QFET®
Rds On (Max) @ Id, Vgs	1.55 Ohm @ 4.2A, 10V
Power Dissipation (Max)	220W (Tc)
Packaging	Tube
Package / Case	TO-3P-3, SC-65-3
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Through Hole
Input Capacitance (Ciss) (Max) @ Vds	2050pF @ 25V
Gate Charge (Qg) (Max) @ Vgs	45nC @ 10V
FET Type	N-Channel
FET Feature	-
Drain to Source Voltage (Vdss)	800V
Current - Continuous Drain (Id) @ 25°C	8.4A (Tc)

In:

ON Semiconductor®

FQA8N80C
AMI Semiconductor / ON
Semiconductor
MOSFET N-CH 800V 8.4A TO-3P

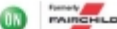
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FQA8N80
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FQA8N100C MOS

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FAIRCHILD TO-3P

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More

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